

**TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))**

Docket No.
SEC.1100

In Re Application Of: **Young-man HWANG et al.**

Serial No.	Filing Date	Examiner	Group Art Unit
NEW	MARCH 1, 2004	TO BE ASSIGNED	TO BE ASSIGNED

Title: PHASE-CHANGE MEMORY AND METHOD HAVING RESTORE FUNCTION

Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

the statement specified in 37 CFR 1.97(e);

OR

the fee set forth in 37 CFR 1.17(p).

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PHASE-CHANGE MEMORY AND METHOD HAVING RESTORE FUNCTION

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

A check in the amount of _____ is attached.
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Dated: **MARCH 1, 2004**

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) SEC.1100		Application Number NEW		
				Applicant(s) Young-nam HWANG et al.		Filing Date MARCH 1, 2004		Group Art Unit TO BE ASSIGNED
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
	A	6,545,907	04/08/2003	LOWREY et al.				
	B	2003/0002332	01/02/2003	LOWREY				
	C	6,487,113	11/26/2002	PARK et al.				
	D	6,075,719	06/13/2000	LOWREY et al.				
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
	E	Y.N. Hwang et al., "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors"						
	F	Manzur Gill et al., "Ovonic Unified Memory - A High-Performance Nonvolatile Memory Technology for Stand-Alone Memory and Embedded Applications," ISSCC 2002/Session 12/TD: Digital Directions/12.4, pages 158-159, and 445-446.						
EXAMINER				DATE CONSIDERED				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								

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		Applicant(s) Young-man HWANG et al.	
		Filing Date March 1, 2004	Group Art Unit TO BE ASSIGNED
*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
G	Stefan Lai et al., "OUM - A 180 nm Nonvolatile Memory Cell Element Technology For Stand Alone and Embedded Applications," IEDM 01-803 - 806.		
H	Y.N. Hwang et al., "Phase-Change Chalcogenide Nonvolatile RAM Completely Based on CMOS Technology"		
I	Linda Geppert, "The New Indelible Memories," IEEE Spectrum, March 2003, pages 49-54.		
J	Jon Maimon et al., "Chalcogenide-Based Non-Volatile Memory Technology," pages 5-2289 - 5-2294.		
EXAMINER	DATE CONSIDERED		

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